

Excellent Integrated System Limited

Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-5EWH06FNHM3</u>

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Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-5EWH06FNHM3 - DIODE FRED 600V 5A DPAK

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VS-5EWH06FNHM3

Vishay Semiconductors

Hyperfast Rectifier, 5 A FRED Pt®

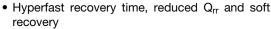


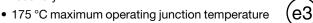


D-PAK (TO-252AA)

PRODUCT SUMMARY				
Package	D-PAK (TO-252AA)			
I _{F(AV)}	5 A			
V_{R}	600 V			
V _F at I _F	1.85 V			
t _{rr} (typ.)	18 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES





HALOGEN

FREE

- For PFC CRM/CCM operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Material categorization: For definitions of compliance please see www.vishav.com/doc?99912



State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		600	V	
Average rectified forward current	I _{F(AV)}	T _C = 150 °C	5		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	70	А	
Peak repetitive forward current	I _{FM}	$T_C = 150 ^{\circ}\text{C}, f = 20 \text{kHz}, d = 50 \%$	10		
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-	
Forward voltage		I _F = 5 A	-	1.54	1.85	V
Forward voltage V _F	I _F = 5 A, T _J = 150 °C	-	1.20	1.40		
Doverno lookogo gurrent	_	$V_R = V_R$ rated	-	-	5	
Reverse leakage current I _R		T _J = 150 °C, V _R = V _R rated	-	-	130	μA
Junction capacitance	C _T	V _R = 600 V	-	3.5	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8 -		nH		

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Datasheet of VS-5EWH06FNHM3 - DIODE FRED 600V 5A DPAK

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time t _{rr}	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	18	-		
		$I_F = 1 \text{ A, } dI_F/dt = 50 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		-	22	-	ns
	T _J = 25 °C		-	25	-		
	T _J = 125 °C		-	35	-		
Peak recovery current I _{RRM}		T _J = 25 °C	$I_F = 5 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	3.9	-	А
	IRRM	T _J = 125 °C		-	5.1	-	
Reverse recovery charge Q _{rr}		T _J = 25 °C		-	51	-	nC
	T _J = 125 °C		-	93	-	110	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C
Thermal resistance, junction to case per leg	R_{thJC}		-	-	3	°C/W
Approximate weight				0.3		g
Approximate weight				0.01		OZ.
Marking device		Case style D-PAK (TO-252AA)		5EWH	06FNH	

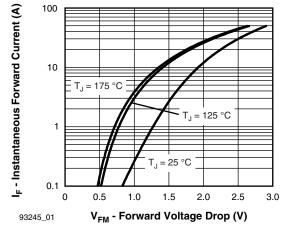


Fig. 1 - Typical Forward Voltage Drop Characteristics

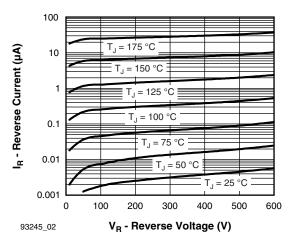


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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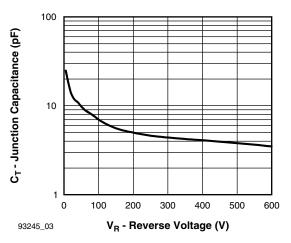


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

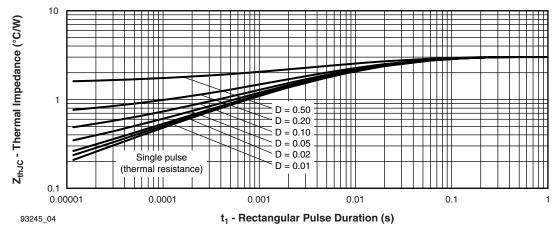


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

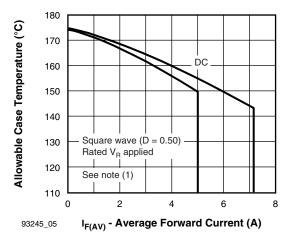


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

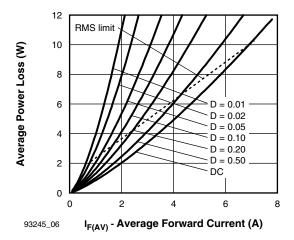


Fig. 6 - Forward Power Loss Characteristics

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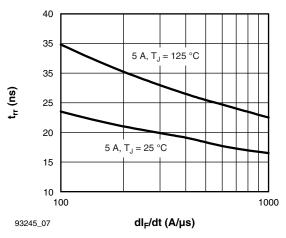


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

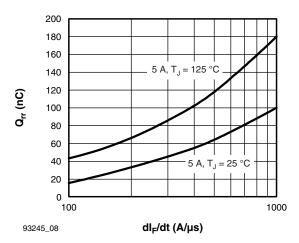
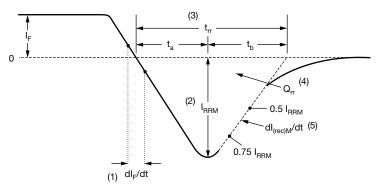


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{l} \text{(1)} \ \ \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \ \text{at } (I_{F(AV)}/D) \ \text{(see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \ \text{(1 - D); } I_R \ \text{at } V_{R1} = Rated \ V_R \\ \end{array}$



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_F$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

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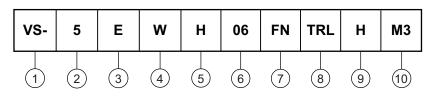


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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Current rating (5 = 5 A)

Circuit configuration:

E = Single diode

4 - Package identifier:

W = D-PAK

5 - H = Hyperfast recovery

- Voltage rating (06 = 600 V)

7 - FN = TO-252AA

8 - • None = Tube

• TR = Tape and reel

• TRL = Tape and reel (left oriented)

• TRR = Tape and reel (right oriented)

9 - H = AEC-Q101 qualified

10 - Environmental digit:

M3 = Halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-5EWH06FNHM3	75	3000	Antistatic plastic tube		
VS-5EWH06FNTRHM3	2000	2000	13" diameter reel		
VS-5EWH06FNTRLHM3	3000	3000	13" diameter reel		
VS-5EWH06FNTRRHM3	3000	3000	13" diameter reel		

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95519</u>				
Part marking information	www.vishay.com/doc?95176			
Packaging information	www.vishay.com/doc?95518			
SPICE model	www.vishay.com/doc?95186			



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